



30V P-Channel Enhancement Mode MOSFET

Voltage

-30 V

Current

-90A

Features

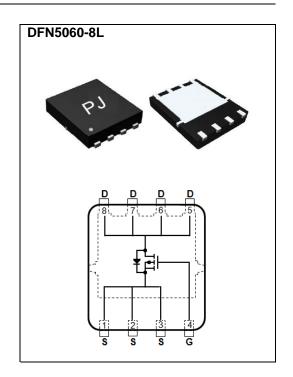
- $R_{DS(ON)}$, $V_{GS}@-10V$, $I_D@-20A<4.5m\Omega$
- $R_{DS(ON)}$, $V_{GS}@-4.5V$, $I_D@-15A<7m\Omega$
- High switching speed
- Improved dv/dt capability
- Low Gate Charge
- Low reverse transfer capacitance
- Lead free in compliance with EU RoHS 2011/65/EU directive.
- Green molding compound as per IEC61249 Std.. (Halogen Free)

Mechanical Data

• Case: DFN5060-8L Package

• Terminals: Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.0028 ounces, 0.08 grams



Maximum Ratings and Thermal Characteristics (T_A=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V_{DS}	-30	V	
Gate-Source Voltage		V_{GS}	<u>+</u> 20	V	
Continuous Drain Current	T _C =25°C	l _D	-90	А	
	T _C =100°C		-57		
Pulsed Drain Current(Note 1)	T _C =25°C	I _{DM}	-360		
Power Dissipation	T _C =25°C	Po	60	W	
	T _C =100°C		24		
Continuous Drain Current	T _A =25°C	I _D	-15.8	Α	
	T _A =70°C		-12.6	Α	
Power Dissipation	T _A =25°C	1	2	W	
Power Dissipation	T _A =70°C	Pb	1.3		
Operating Junction and Storage Temperature Range		T_J, T_{STG}	-55~150	°C	
Typical Thermal resistance (Note 4,5)	Junction to Case	$R_{ heta JC}$	2.1	°C/W	
	Junction to Ambient	$R_{ heta JA}$	62.5		

Limited only By Maximum Junction Temperature





Electrical Characteristics (T_A=25 °C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS		
Static								
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V,I _D =-250uA	-30	-	-	V		
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_{D}=-250$ uA	-1	-1.6	-2.5	V		
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =-10V,I _D =-20A	-	3.9	4.5	mΩ		
		V _{GS} =-4.5V,I _D =-15A	-	5.7	7			
Zero Gate Voltage Drain Current	I _{DSS}	V_{DS} =-30V, V_{GS} =0V	-	-	-1	uA		
Gate-Source Leakage Current	I _{GSS}	V _{GS} = <u>+</u> 20V,V _{DS} =0V	-	-	<u>+</u> 100	nA		
Dynamic (Note 6)								
Total Gate Charge	Q_{g}	V _{DS} =-15V, I _D =-10A, V _{GS} =-10V ^(Note 2,3)	-	107	-	nC		
Gate-Source Charge	Q_gs		-	18	-			
Gate-Drain Charge	Q_{gd}		-	18	-			
Input Capacitance	Ciss	V _{DS} =-25V, V _{GS} =0V,	-	6067	-	pF		
Output Capacitance	Coss		-	709	-			
Reverse Transfer Capacitance	Crss	I=1.UIVIHZ	-	361	-			
Turn-On Delay Time	td _(on)	1/ 451/1 40	-	22	-			
Turn-On Rise Time	t _r	V_{DS} =-15V, I_{D} =-1A, V_{GS} =-10V, R_{G} =6 Ω (Note 2,3)	-	48	-	ns		
Turn-Off Delay Time	td _(off)		-	197	-			
Turn-Off Fall Time	t _f		-	90	-			
Drain-Source Diode								
Maximum Continuous Drain-Source	,				-90	Α		
Diode Forward Current	I _S		-	-	-90	A		
Diode Forward Voltage	V_{SD}	I _S =-1A,V _{GS} =0V	-	-0.68	-1	V		

NOTES:

- 1. Pulse width<a>300us, Duty cycle<a>2%
- 2. Essentially independent of operating temperature typical characteristics
- 3. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$ =150°C. Ratings are based on low frequency and duty cycles to keep initial T_J =25°C.
- 4. The maximum current rating is package limited
- 5. Roja is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
- 6. Guaranteed by design, not subject to production testing





TYPICAL CHARACTERISTIC CURVES

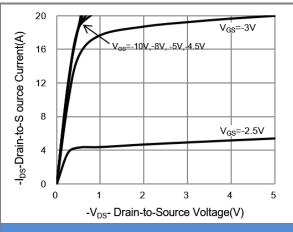


Fig.1 On-Region Characteristics

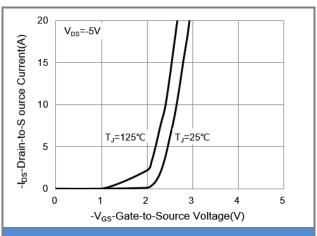


Fig.2 Transfer Characteristics

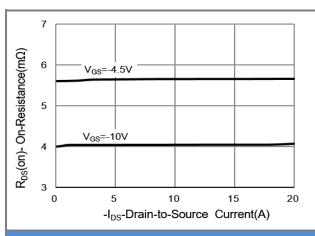


Fig.3 On-Resistance vs. Drain Current

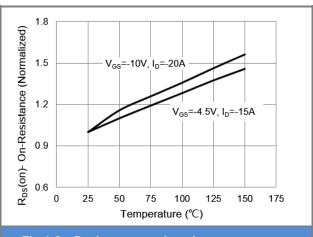


Fig.4 On-Resistance vs. Junction temperature

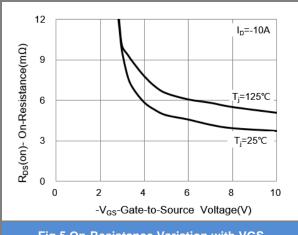


Fig.5 On-Resistance Variation with VGS.

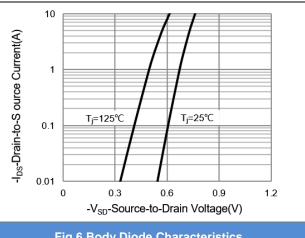


Fig.6 Body Diode Characteristics





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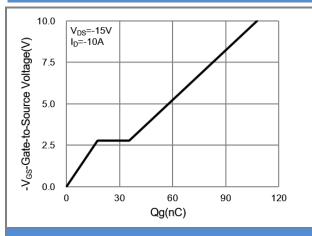


Fig.7 Gate-Charge Characteristics

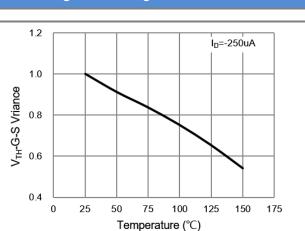
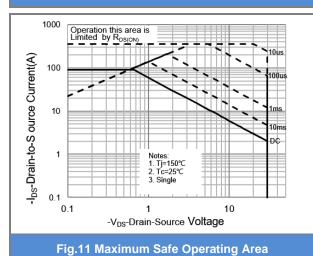


Fig.9 Threshold Voltage Variation with Temperature



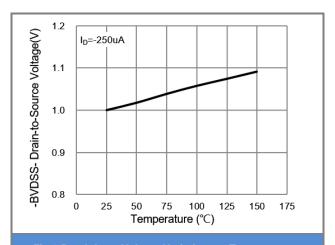


Fig.8 Breakdown Voltage Variation vs. Temperature

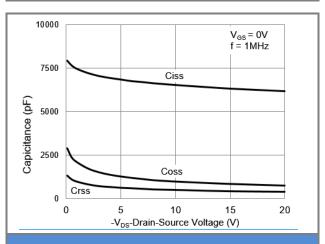


Fig.10 Capacitance vs. Drain-Source Voltage





TYPICAL CHARACTERISTIC CURVES

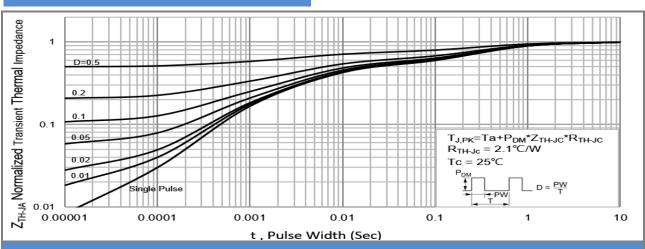


Fig.12 Normalized Transient Thermal Impedance vs. Pulse Width

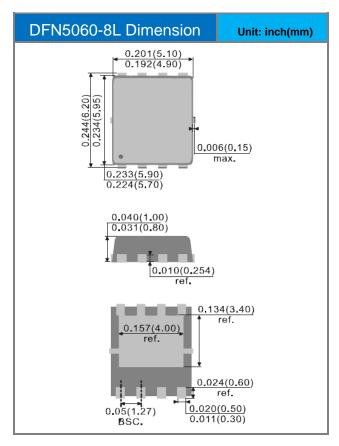


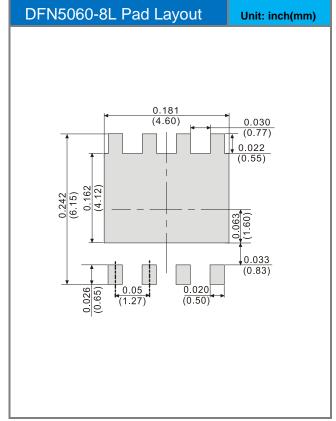


Part No Packing Code Version

Part No Packing Code	Package Type	Packing Type	Marking	Version	
PJQ5425_R2_00001	DFN5060-8L	3000pcs / 13" reel	Q5425	Halogen free	

Packaging Information & Mounting Pad Layout









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